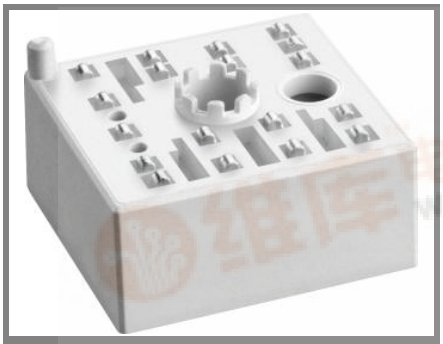
SKiiP 01NEB066V3



MiniSKiiP® 0

1-phase bridge rectifier + brake chopper + 3-phase bridge inverter

SKiiP 01NEB066V3

Features

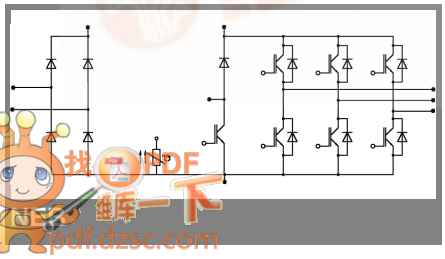
- Trench IGBT´s
- Robust and soft freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised file no. E63532

Typical Applications

- Inverter up to 3,5 kVA
- Typical motor power 1,5 kW

Remarks

- Case temperature limited to T_C = 125°C max.
- Product reliability results are valid for T_j = 150°C
- SC data: $t_p \leq 6$ µs; $V_{GE} \leq 15$ V; T_j = 150°C; V_{CC} = 360 V
- V_{CEsat}, V_F = chip level value



Absolute Maximum Ratings T_s = 25 °C, unless otherwise specified

Symbol	Conditions	Values	Units
IGBT - Inverter, Chopper			
V_{CES}		600	V
I_C	T_s = 25 (70) °C, T_j = 150 °C	12 (12)	A
I_C	T_s = 25 (70) °C, T_j = 175 °C	12 (12)	A
I_{CRM}	t_p = 1 ms	12	A
V_{GES}		± 20	V
Diode - Inverter, Chopper			
I_F	T_s = 25 (70) °C, T_j = 150 °C	12 (12)	A
I_F	T_s = 25 (70) °C, T_j = 175 °C	12 (12)	A
I_{FRM}	t_p = 1 ms	12	A
Diode - Rectifier			
V_{RRM}		800	V
I_F	T_s = 70 °C	35	A
I_{FSM}	t_p = 10 ms, sin 180 °, T_j = 25 °C	220	A
i^2t	t_p = 10 ms, sin 180 °, T_j = 25 °C	240	A²s
I_{tRMS}	per power terminal (20 A / spring)	20	A
T_j	IGBT, Diode	-40...+175	°C
T_{stg}		-40...+125	°C
V_{isol}	AC, 1 min.	2500	V

Characteristics T_s = 25 °C, unless otherwise specified

Symbol	Conditions	min.	typ.	max.	Units
IGBT - Inverter, Chopper					
$V_{CE(sat)}$	I_{Cnom} = 6 A, T_j = 25 (150) °C		1,45 (1,65)	1,85 (2,05)	V
$V_{GE(th)}$	V_{GE} = V_{CE}, I_C = 1 mA		5,8		V
$V_{CE(TO)}$	T_j = 25 (150) °C		0,9 (0,7)	1,1 (1)	V
r_{CE}	T_j = 25 (150) °C		100 (167)	134 (184)	mΩ
C_{ies}	V_{CE} = 25 V, V_{GE} = 0 V, f = 1 MHz		0,45		nF
C_{oes}	V_{CE} = 25 V, V_{GE} = 0 V, f = 1 MHz		0,1		nF
C_{res}	V_{CE} = 25 V, V_{GE} = 0 V, f = 1 MHz		0,05		nF
$R_{CC'+EE'}$	spring contact-chip T_s = 25 (150)°C				mΩ
$R_{th(j-s)}$	per IGBT		2,4		K/W
$t_{d(on)}$	under following conditions		20		ns
t_r	V_{CC} = 300 V, V_{GE} = -8V/+15V		25		ns
$t_{d(off)}$	I_{Cnom} = 6 A, T_j = 150 °C		175		ns
t_f	R_{Gon} = R_{Goff} = 47 Ω		60		ns
E_{on} (E_{off})	inductive load		0,3 (0,2)		mJ
Diode - Inverter, Chopper					
V_F = V_{EC}	I_F = 6 A, T_j = 25 (150) °C		1,3 (1,3)	1,6 (1,6)	V
$V_{(TO)}$	T_j = 25 (150) °C		0,9 (0,8)	1 (0,9)	V
r_T	T_j = 25 (150) °C		67 (83)	100 (117)	mΩ
$R_{th(j-s)}$	per diode		3		K/W
I_{RRM}	under following conditions		11,2		A
Q_{rr}	I_{Fnom} = 6 A, V_R = 600 V		0,9		µC
E_{rr}	V_{GE} = 0 V, T_j = 150°C		0,2		mJ
	di_F/dt = 520 A/µs				
Diode - Rectifier					
V_F	I_{Fnom} = 15 A, T_j = 25 °C		1,1		V
$V_{(TO)}$	T_j = 150 °C		0,8		V
r_T	T_j = 150 °C		20		mΩ
$R_{th(j-s)}$	per diode		1,5		K/W
Temperature Sensor					
R_{ts}	3 %, T_r = 25 (100) °C		1000(1670)		Ω
Mechanical Data					
w			21,5		g
M_s	Mounting torque	2		2,5	Nm

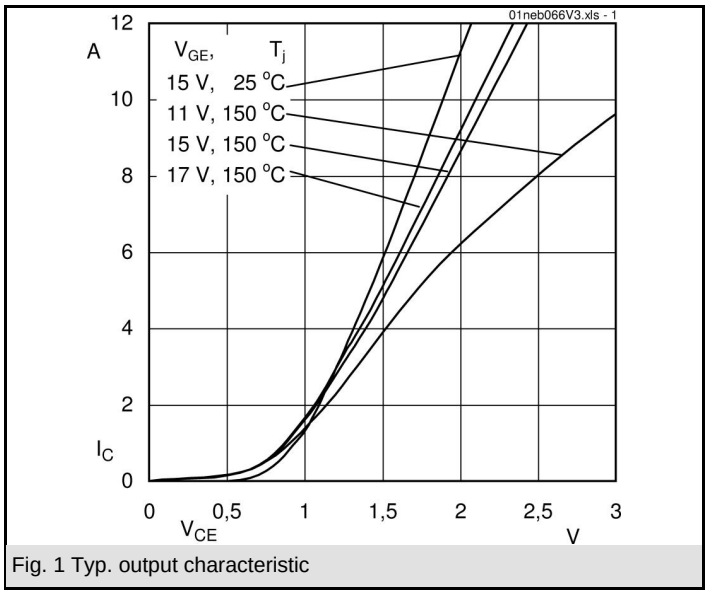


Fig. 1 Typ. output characteristic

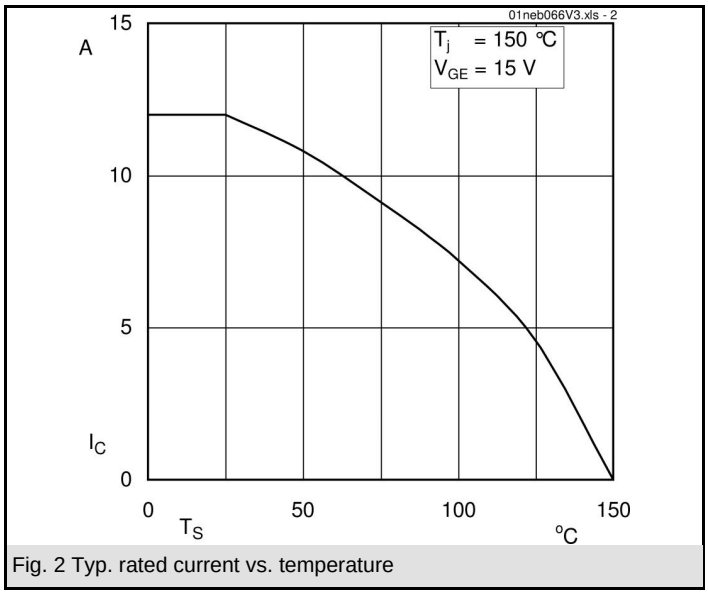


Fig. 2 Typ. rated current vs. temperature

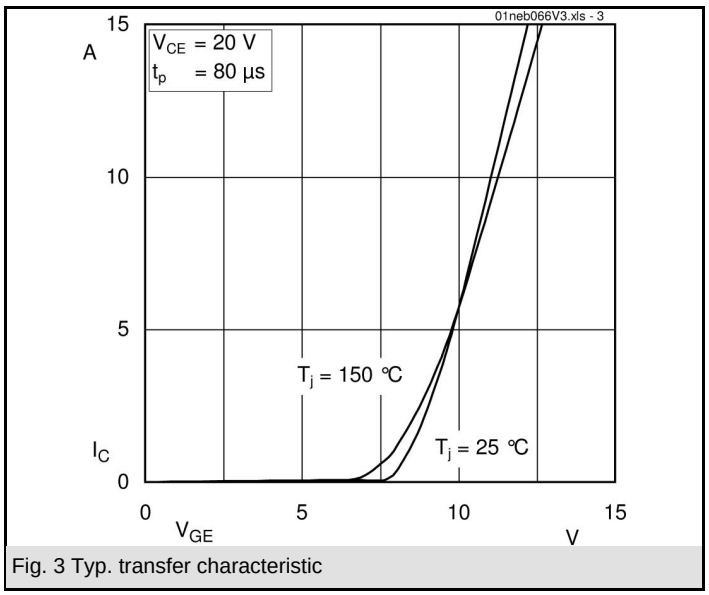


Fig. 3 Typ. transfer characteristic

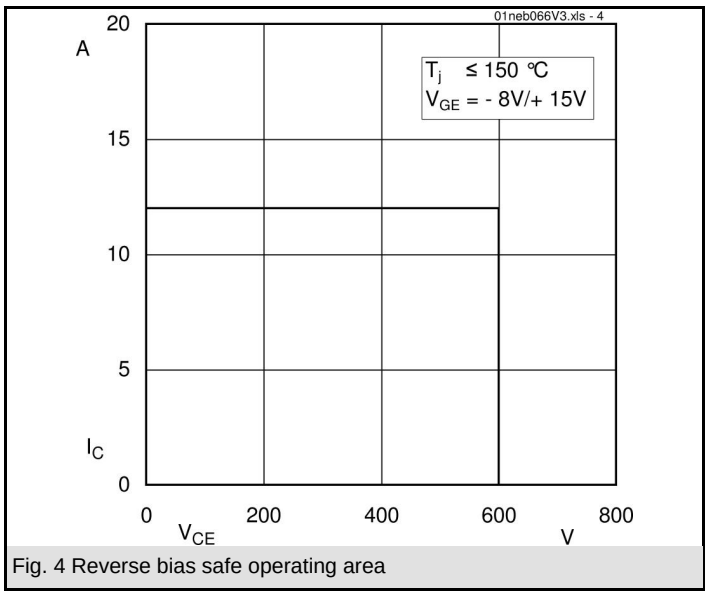


Fig. 4 Reverse bias safe operating area

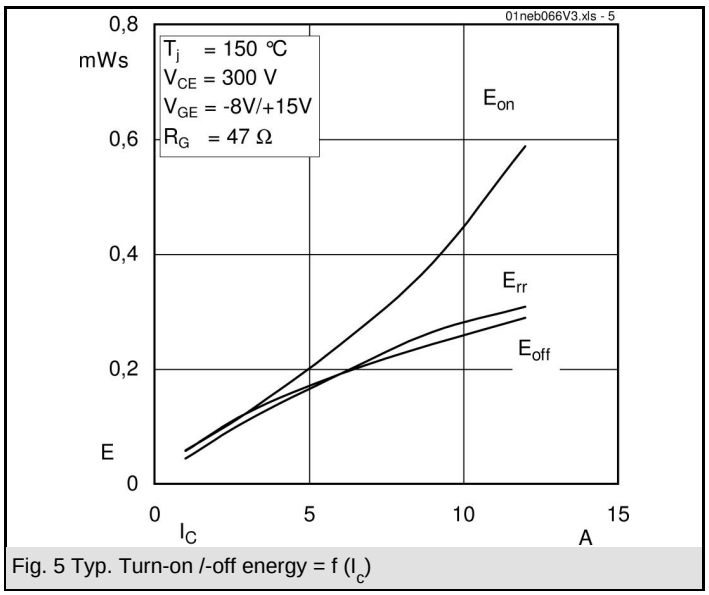


Fig. 5 Typ. Turn-on /-off energy = f (I_c)

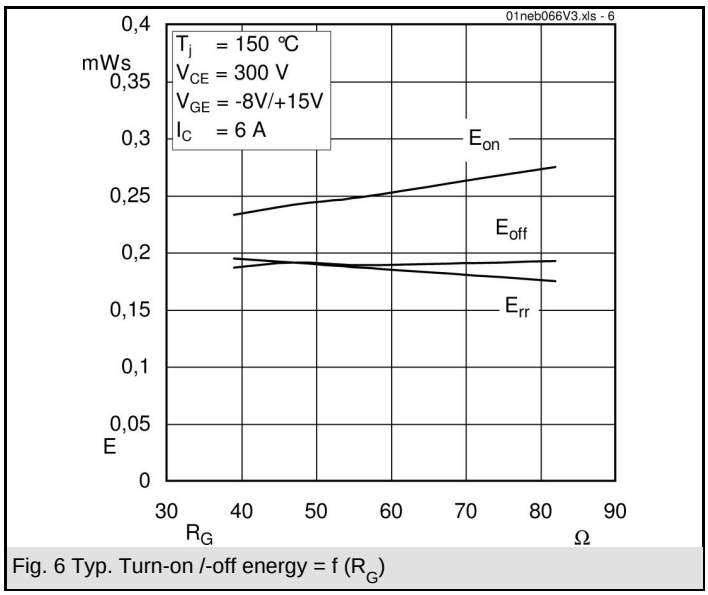


Fig. 6 Typ. Turn-on /-off energy = f (R_G)

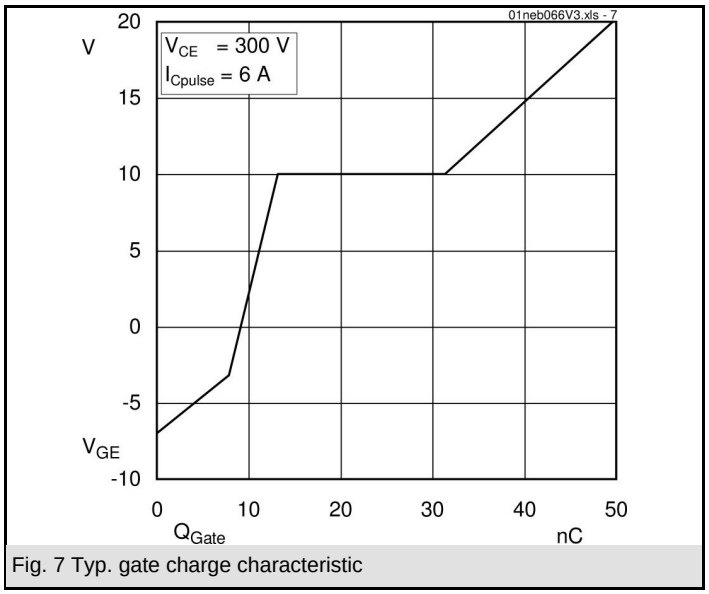


Fig. 7 Typ. gate charge characteristic

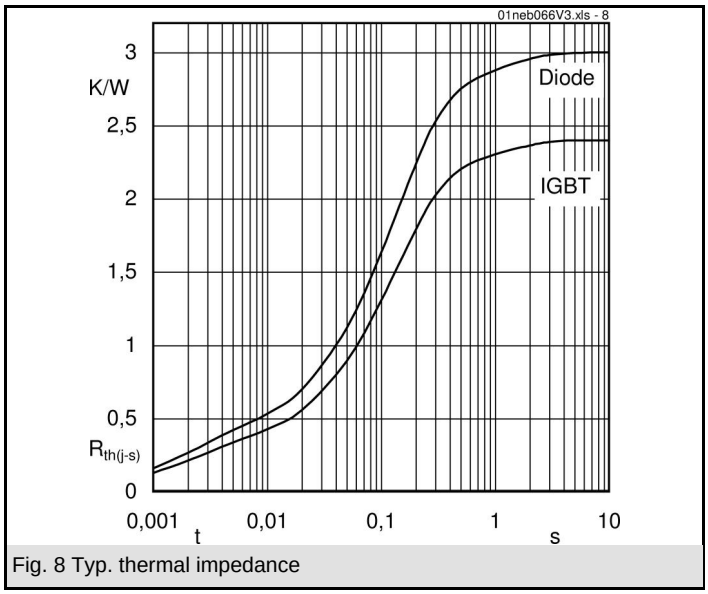


Fig. 8 Typ. thermal impedance

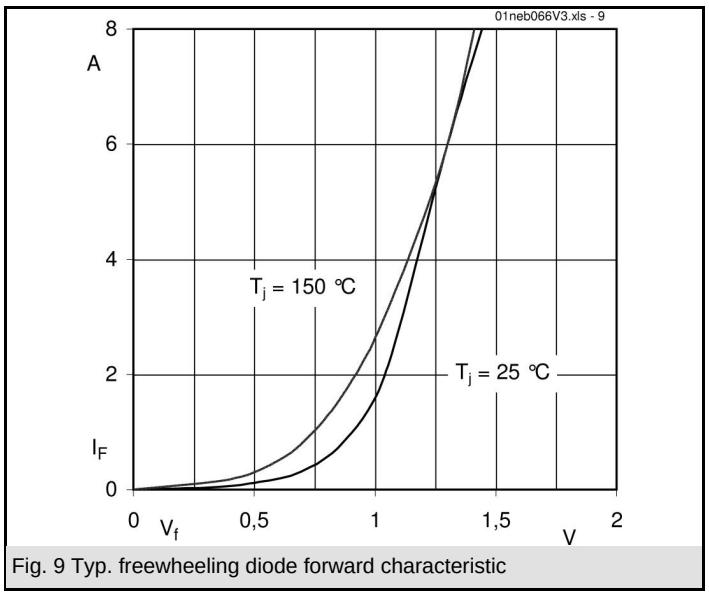


Fig. 9 Typ. freewheeling diode forward characteristic

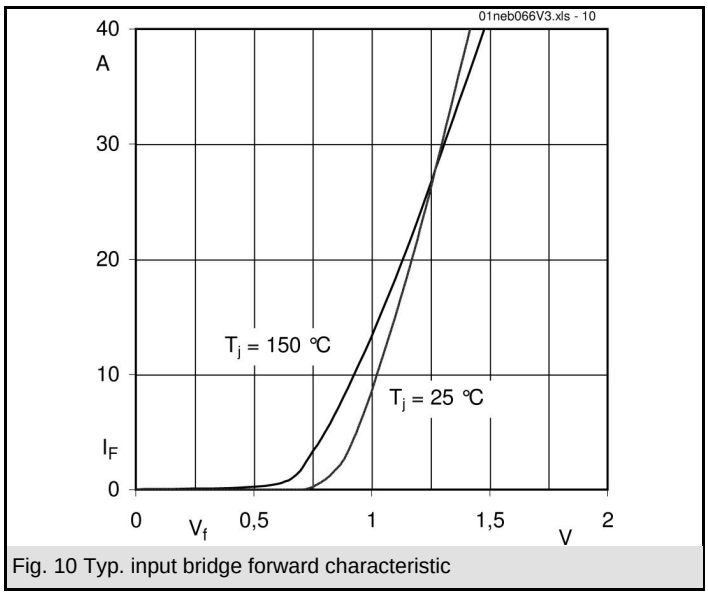


Fig. 10 Typ. input bridge forward characteristic

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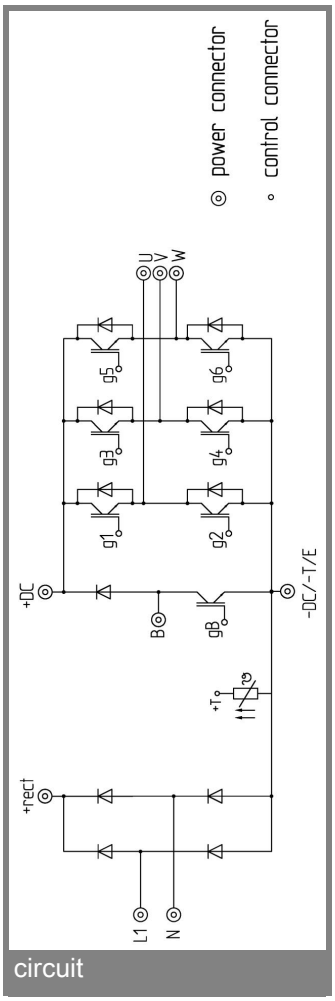
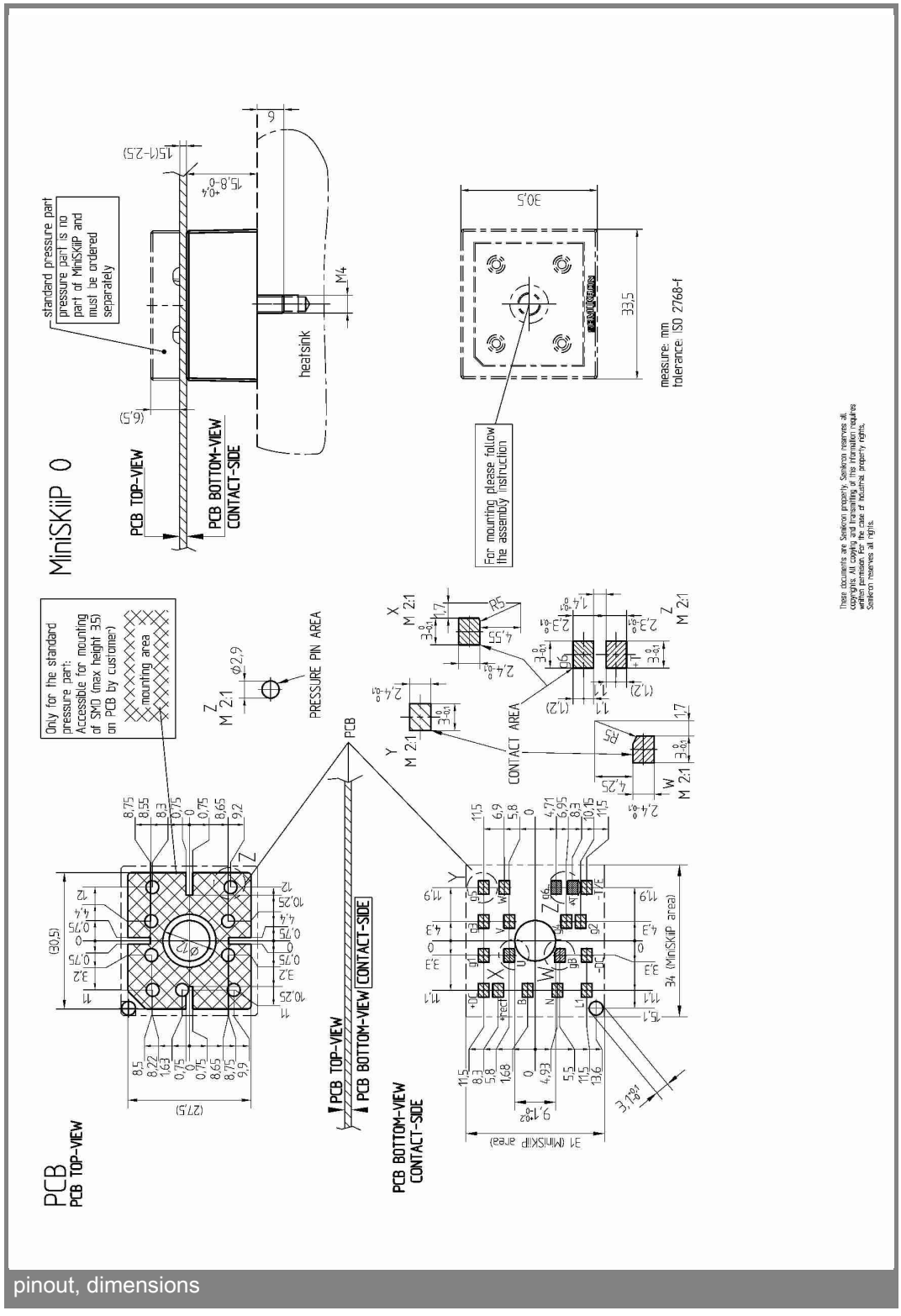


circuit



pinout, dimensions

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

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